

## IGBT Chip in NPT-technology

### FEATURES:

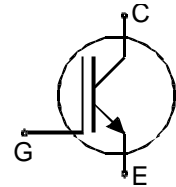
- 1200V NPT technology
- 180µm chip
- low turn-off losses
- short tail current
- positive temperature coefficient
- easy paralleling

### This chip is used for:

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### Applications:

- drives, SMPS, resonant applications



Chip Type	V <sub>CE</sub>	I <sub>Cn</sub>	Die Size	Package	Ordering Code
SIGC25T120CS	1200V	15A	5.71 x 4.53 mm <sup>2</sup>	sawn on foil	Q67050-A4114

### MECHANICAL PARAMETER:

Raster size	5.71 x 4.53	mm <sup>2</sup>
Emitter pad size	2 x (2.18 x 1.6)	
Gate pad size	1.09 x 0.68	
Area total / active	25.9 / 18.7	
Thickness	180	µm
Wafer size	150	mm
Flat position	270	grd
Max.possible chips per wafer	555 pcs	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm Al Si 1%	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, <500µm	
Reject Ink Dot Size	Ø 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

## MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j=25\text{ °C}$	$V_{CE}$	1200	V
DC collector current, limited by $T_{jmax}$	$I_C$	<sup>1)</sup>	A
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	45	A
Gate emitter voltage	$V_{GE}$	$\pm 20$	V
Operating junction and storage temperature	$T_j, T_{stg}$	-55 ... +150	°C

<sup>1)</sup> depending on thermal properties of assembly

## STATIC CHARACTERISTICS (tested on chip), $T_j=25\text{ °C}$ , unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=1mA$	1200			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=15A$	2.5	3.0	3.6	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=0.6mA, V_{GE}=V_{CE}$	3.0	4.0	5.0	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$			2	µA
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$			480	nA

## ELECTRICAL CHARACTERISTICS (tested at component):

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	$C_{iss}$	$V_{CE}=25V,$	-	1250		pF
Output capacitance	$C_{oss}$	$V_{GE}=0V,$	-	100		
Reverse transfer capacitance	$C_{riss}$	$f=1MHz$	-	65		

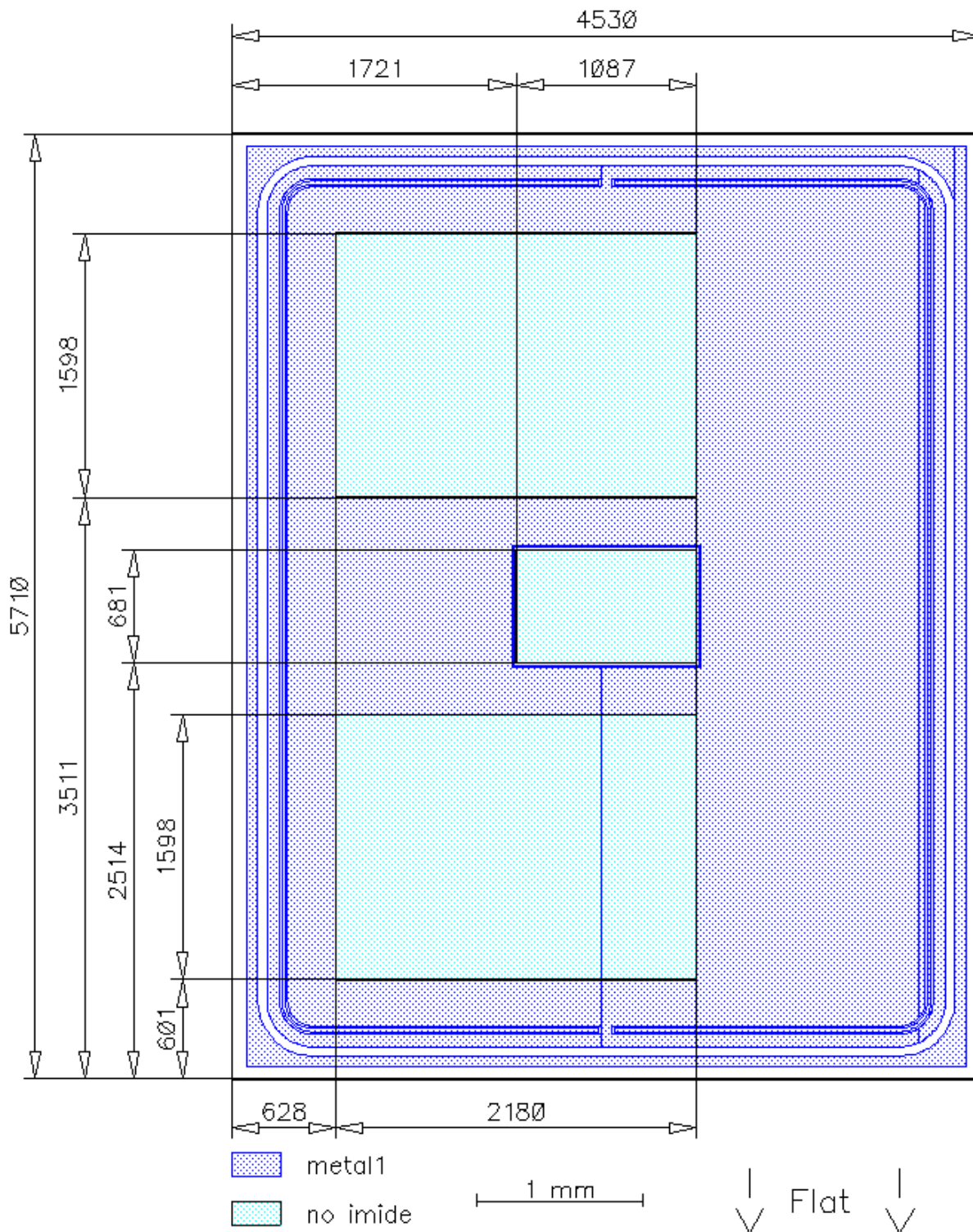
## SWITCHING CHARACTERISTICS (tested at component), Inductive Load

Parameter	Symbol	Conditions <sup>1)</sup>	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	$T_j=150\text{ °C}$	-	38		ns
Rise time	$t_r$	$V_{CC}=800V,$	-	30		
Turn-off delay time	$t_{d(off)}$	$I_C=15A,$	-	652		
Fall time	$t_f$	$V_{GE}=-15/15V,$ $R_G=33\Omega$	-	31		

<sup>1)</sup> values also influenced by parasitic L- and C- in measurement and package.

**CHIP DRAWING:**

Die-Size 4530 um x 5710 um





# SIGC25T120CS

## FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the device data sheet		SGP15N120
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## DESCRIPTION:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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